

20V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
	90mΩ @ V _{GS} = -4.5V	-3.1A
-20V	250mΩ @ V _{GS} = -2.5V	-1.8A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors

Features and Benefits

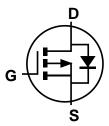
- Low On-Resistance
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

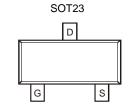
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (§3)
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)







Internal Schematic



Top View

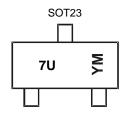
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2170U-7	SOT23	3,000/Tape & Reel
DMP2170U-13	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



7U = Product Type Marking Code YM = Date Code Marking Y or Y= Year (ex: D = 2016) M = Month (ex: 9 = September)

Date Code Key

Year	2016		2017	2018		2019	2020		2021	2022		2023
Code	D		Е	F		G	Н		I	J		K
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Drain-Source Voltage	V_{DSS}	-20	V	
Gate-Source Voltage	V_{GSS}	±12	V	
Continuous Drain Current (Note 6) V _{GS} = -4.5V	I _D	-3.1 -2.5	А	
Maximum Continuous Body Diode Forward Curre	ent (Note 6)	I _S	-1.25	Α
Pulsed Drain Current (10μs pulse, duty cycle = 1	%)	I _{DM}	-13	A

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_{D}	0.78	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	163	°C/W
Total Power Dissipation (Note 6)		P_D	1.28	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ heta JA}$	99	°C/W
Operating and Storage Temperature Range		T_{J}, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	-20	-	-	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	-	-	-1.0	μΑ	$V_{DS} = -20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(TH)}$	-0.4	-1.01	-1.25	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
			62	90		$V_{GS} = -4.5V$, $I_D = -3.5A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	-	92	180	$m\Omega$	$V_{GS} = -2.7V$, $I_{D} = -3.0A$	
	` ,		101	250		$V_{GS} = -2.5V$, $I_D = -2.6A$	
Diode Forward Voltage	V_{SD}	ı	-0.8	-1.1	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	-	303	-	рF	10/1/	
Output Capacitance	Coss	=	46	-	pF	$V_{DS} = -10V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	-	37	-	pF	1 = 1.0WHZ	
Gate Resistance	Rg		16	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Q_g	-	3.6	-	nC		
Total Gate Charge (V _{GS} = -10V)	Qg	-	7.8	-	nC	101/ 1 150	
Gate-Source Charge	Q _{gs}		0.6	-	nC	$V_{DS} = -10V, I_{D} = -1.5A$	
Gate-Drain Charge	Q_{gd}	-	1.1	-	nC		
Turn-On Delay Time	t _{D(ON)}	-	5.4	-	ns		
Turn-On Rise Time	t _R	-	18.3	-	ns	$V_{DD} = -10V, V_{GS} = -4.5V,$	
Turn-Off Delay Time	t _{D(OFF)}	-	16.2	-	ns	$I_D = -3.5A$, $R_G = 6\Omega$	
Turn-Off Fall Time	t _F	-	13.6	-	ns		
Body Diode Reverse Recovery Time	t _{RR}	-	5.5	-	ns	$I_S = -2.0A$, $dI/dt = -100A/\mu s$	
Body Diode Reverse Recovery Charge	Q _{RR}	-	1.23	-	nC	$I_S = -2.0A$, $dI/dt = -100A/\mu s$	

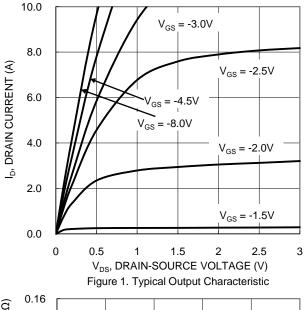
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

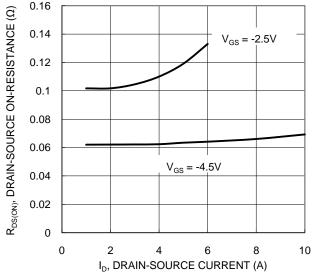
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

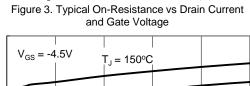
7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.









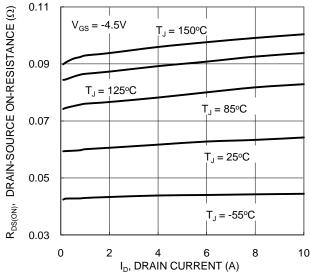


Figure 5. Typical On-Resistance vs Drain Current and Junction Temperature

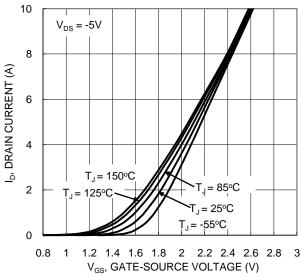
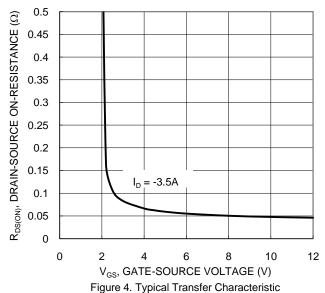


Figure 2. Typical Transfer Characteristic



1.8 R_{DS(ON)}, DRAIN-SOURCE ON-RESISTANCE (NORMALIZED) 1.6 1.4 1.2 1 $V_{GS} = -2.5V, I_{D} = -2.6A$ 8.0 0.6 -50 -25 0 25 50 75 100 125 150 T_J, JUNCTION TEMPERATURE (°C)

Figure 6. On-Resistance Variation with Junction Temperature



 $I_D = -1mA$

75

100

125

150



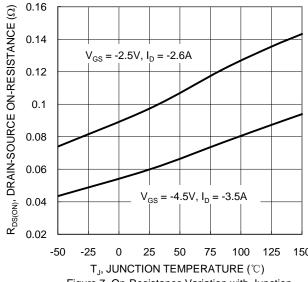
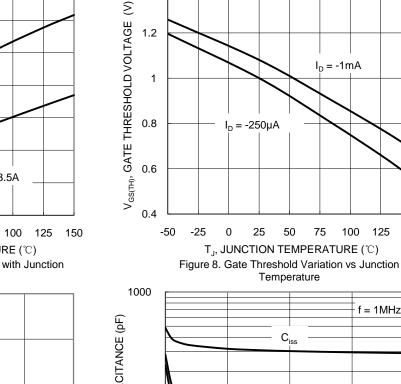
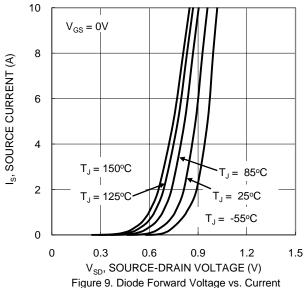


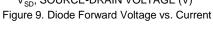
Figure 7. On-Resistance Variation with Junction Temperature

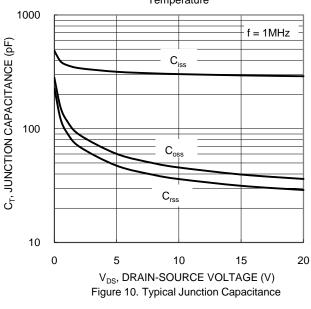


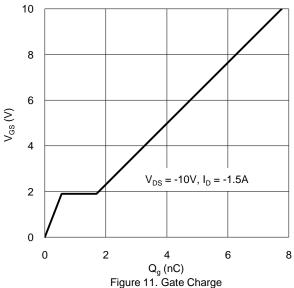
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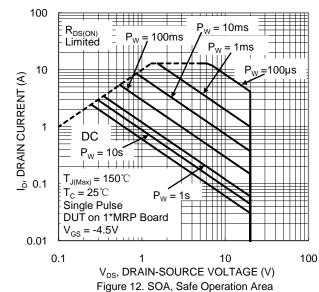
1.2













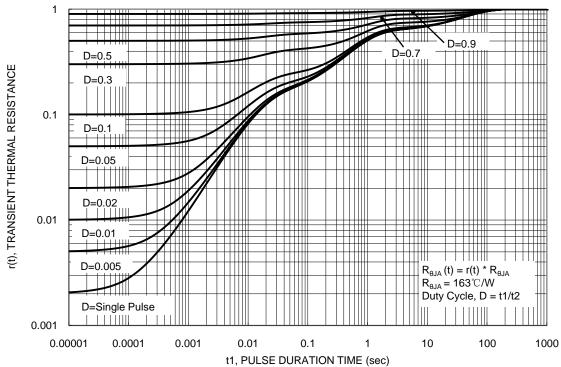


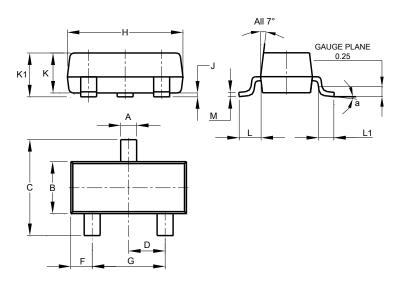
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

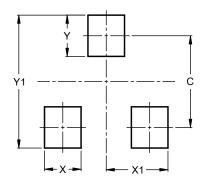


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
C	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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